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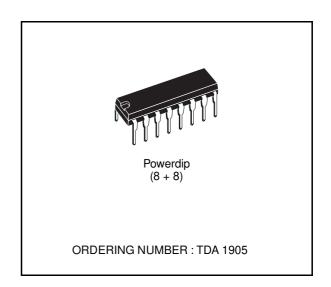
5W AUDIO AMPLIFIER WITH MUTING

DESCRIPTION

The TDA1905 is a monolithic integrated circuit in POWERDIP package, intended for use as low frequency power amplifier in a wide range of applications in radio and TV sets:

- muting facility
- protection against chip over temperature
- very low noise
- high supply voltage rejection
- low "switch-on" noise
- voltage range 4V to 30V

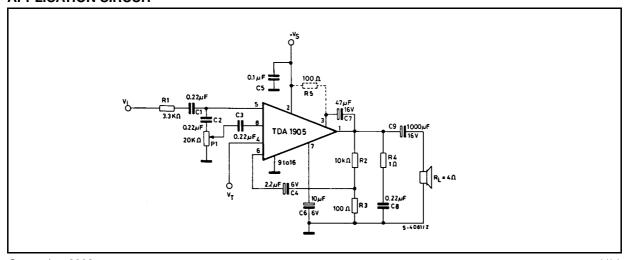
The TDA 1905 is assembled in a new plastic package, the POWERDIP, that offers the same assembly ease, space and cost saving of a normal dual in-line package but with a power dissipation of up to 6W and a thermal resistance of 15°C/W (junction to pins).



ABSOLUTE MAXIMUM RATINGS

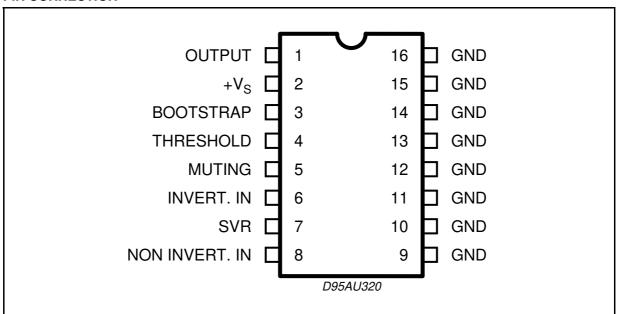
Symbol	Parameter	Value	Unit
Vs	Supply voltage	30	V
I _o	Output peak current (non repetitive)	3	Α
Ιο	Output peak current (repetitive)	2.5	Α
Vi	Input voltage	$0 \text{ to } + V_s$	V
Vi	Differential input voltage	± 7	V
V ₁₁	Muting thresold voltage	V_s	V
P _{tot}	Power dissipation at T _{amb} = 80°C	1	W
	$T_{case} = 60^{\circ}C$	6	W
T_{stg},T_{j}	Storage and junction temperature	-40 to 150	°C

APPLICATION CIRCUIT

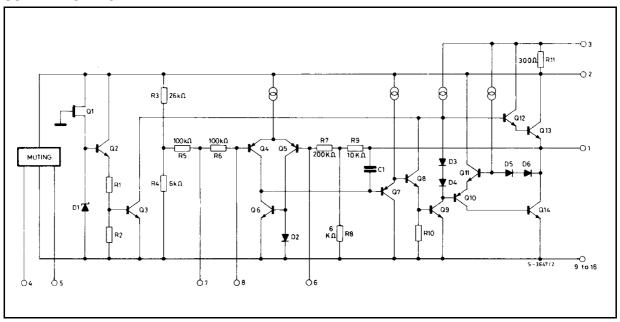


September 2003

PIN CONNECTION



SCHEMATIC DIAGRAM

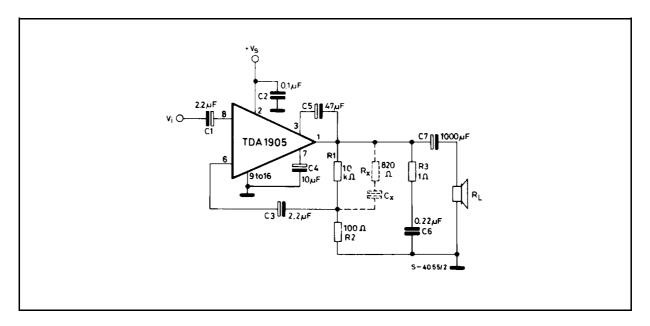


THERMAL DATA

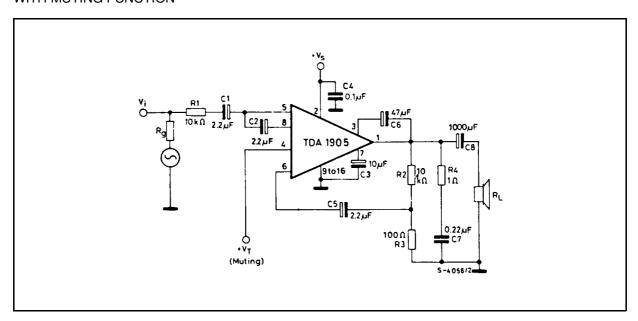
Symbol	Parameter	Value	Unit
R _{th-j-case}	Thermal resistance junction-pins max	15	°C/W
R _{th-j-amb}	Thermal resistance junction-ambient max	70	°C/W

TEST CIRCUITS:

WITHOUT MUTING



WITH MUTING FUNCTION



ELECTRICAL CHARACTERISTICS (Refer to the test circuit, $T_{amb} = 25$ °C, R_{th} (heatsink) = 20 °C/W, unless otherwisw specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Vs	Supply voltage		4		30	V
Vo	Quiescent output voltage	V _S = 4V V _S = 14V V _S = 30V	1.6 6.7 14.4	2.1 7.2 15.5	2.5 7.8 16.8	V
l _d	Quiescent drain current	V _S = 4V V _S = 14V V _S = 30V		15 17 21	35	mA
V _{CE} sat	Output stage saturation voltage	I _C = 1A I _C = 2A		0.5 1		V
P ₀	Output power	$\begin{array}{lll} d = 10\% & f = 1 \text{KHz} \\ V_S = 9V & R_L = 4\Omega \ (^*) \\ V_S = 14V & R_L = 4\Omega \\ V_S = 18V & R_L = 8\Omega \\ V_S = 24V & R_L = 16\Omega \end{array}$	2.2 5 5 4.5	2.5 5.5 5.5 5.3		W
d	Harmonic distortion	$\begin{array}{c} f = 1 \text{KHz} \\ V_s = 9 \text{V} & R_L = 4 \Omega \\ P_o = 50 \text{ mW to } 1.5 \text{W} \\ V_s = 14 \text{V} & R_L = 4 \Omega \\ P_o = 50 \text{ mW to } 3 \text{W} \\ V_s = 18 \text{V} & R_L = 8 \Omega \\ P_o = 50 \text{ mW to } 3 \text{W} \\ V_s = 24 \text{V} & R_L = 16 \Omega \\ P_o = 50 \text{ mW to } 3 \text{W} \\ \end{array}$		0.1 0.1 0.1 0.1		%
Vi	Input sensitivity	$ \begin{array}{llllllllllllllllllllllllllllllllllll$		37 49 73 100		mV
Vi	Input saturation voltage (rms)	V _S = 9V V _S = 14V V _S = 18V V _S = 24V	0.8 1.3 1.8 2.4			V
Ri	Input resistance (pin 8)	f = 1KHz	60	100		ΚΩ
I _d	Drain current	$ \begin{array}{llllllllllllllllllllllllllllllllllll$		380 550 410 295		mA
η	Efficiency	$ \begin{array}{llllllllllllllllllllllllllllllllllll$		73 71 74 75		%

^(*) With an external resistor of 100Ω between pin 3 and +Vs.

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Te	est condition	าร	Min.	Тур.	Max.	Unit
BW	Small signal bandwidth (-3dB)	V _s = 14V	$R_L = 4\Omega$	$P_0 = 1W$	40 to 40,000		Hz	
G _v	Voltage gain (open loop)	$V_s = 14V$ f = 1KHz				75		dB
Gv	Voltage gain (closed loop)	V _s = 14V f = 1KHz	$\begin{array}{l} R_L = 4\Omega \\ P_o = 1W \end{array}$		39.5	40	40.5	dB
e _N	Total input noise		$R_g = 50\Omega$ $R_g = 1K\Omega$ $R_g = 10K\Omega$	(°)		1.2 1.3 1.5	4.0	μV
			$R_g = 50\Omega$ $R_g = 1K\Omega$ $R_g = 10K\Omega$	(°°)		2.0 2.0 2.2	6.0	μV
S/N	Signal to noise ratio	$V_s = 14V$ $P_0 = 5.5W$	$R_g = 10K\Omega$ $R_g = 0$	(°)		90 92		dB
		$R_L = 4\Omega$	$R_g = 10K\Omega$ $R_g = 0$	(°°)		87 87		dB
SVR	Supply voltage rejection	$V_s = 18V$ $f_{ripple} = 100$ $V_{ripple} = 0.5$	Hz F	Rg = 10KΩ	40	50		dB
T _{sd}	Thermal shut-down case temperatura (*)		P _{tot} =	: 2.5W		115		°C

MUTING FUNCTION

VT _{OFF}	Muting-off threshold voltage (pin 4)		1.9		4.7	V
VT _{ON}	VT _{ON} Muting-on threshold		0		1.3	V
voltage (pin 4)			6.2		Vs	
R ₅	Input-resistance (pin 5)	Muting off	80	200		ΚΩ
		Muting on		10	30	Ω
R ₄	Input resistance (pin 4)		150			ΚΩ
A _T	Muting attenuation	$R_g + R_1 = 10K\Omega$	50	60		dB

Note:

(°) Weighting filter = curve A.

(°°) Filter with noise bandwidth: 22 Hz to 22 KHz.

(*) See fig. 30 and fig. 31

Figure 1. Quiescent output voltage vs. supply voltage

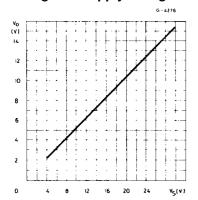


Figure 2. Quiescent drain current vs. supply voltage

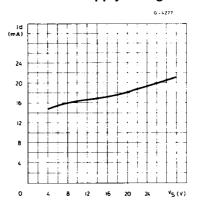


Figure 3. Output power vs. supply voltage

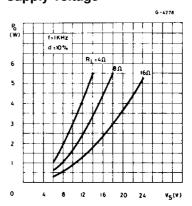


Figure 4. Distortion vs. output power ($R_L = 16\Omega$)

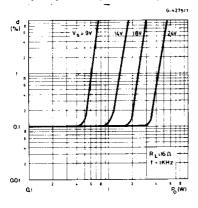


Figure 5. Distortion vs. output power ($R_L = 8\Omega$)

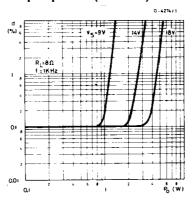


Figure 6. Distortion vs. output power ($R_L = 4\Omega$)

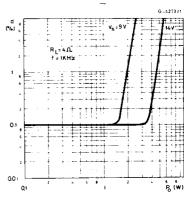
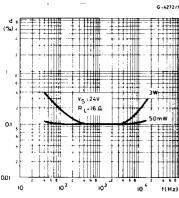


Figure 7. Distortion vs. frequency ($R_L = 16\Omega$)



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Figure 8. Distortion vs. frequency ($R_L = 8\Omega$)

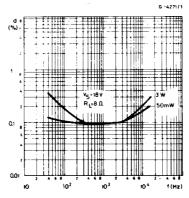
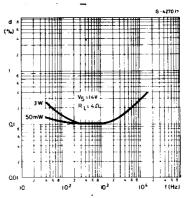


Figure 9. Distortion vs. frequency ($R_L = 4\Omega$)



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Figure 10. Open loop frequency response

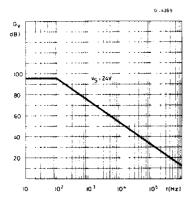


Figure 11. Output power vs. input voltage

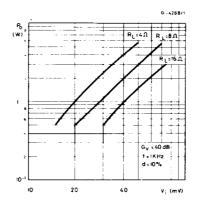


Figure 12. Value of capaci- tor Cx vs. bandwidth (BW) and gain (Gv)

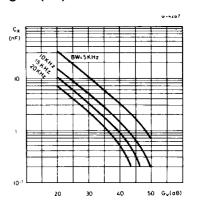


Figure 13. Supply voltage rejection vs. voltage gain (ref. to the Muting circuit)

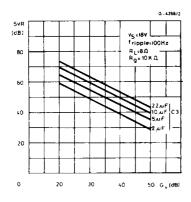


Figure 14. Supply voltage reection vs. source resistance

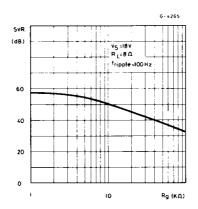


Figure 15. Max power dissipation vs. supply voltage (sine wave operation)

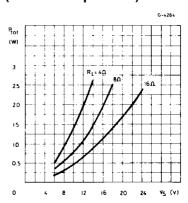


Figure 16. Power dissipation and efficiency vs. output power

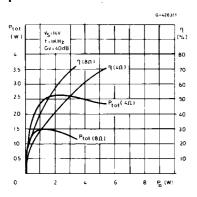


Figure 17. Power dissipation and efficiency vs. output power

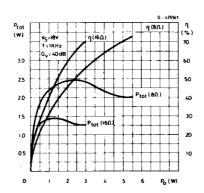
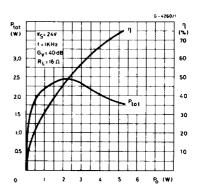


Figure 18. Power dissipation and efficiency vs. output power



APPLICATION INFORMATION

Figure 19. Application circuit without muting

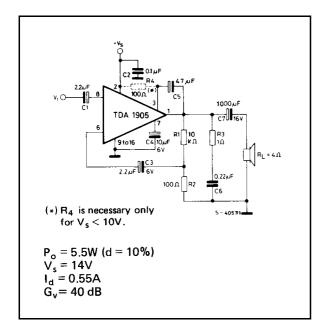


Figure 20. PC board and components lay-out of the circuit of fig. 19 (1 : 1 scale)

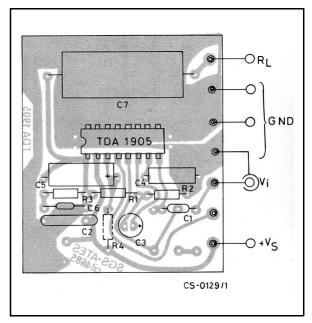


Figure 21. Application circuit with muting

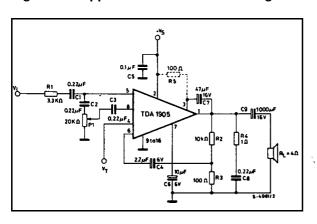
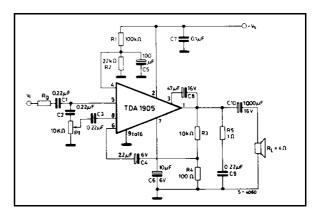


Figure 22. Delayed muting circuit



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APPLICATION INFORMATION (continued)

Figure 23. Low-cost application circuit without bootstrap.

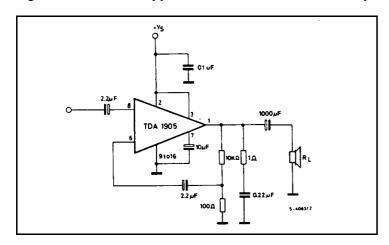


Figure 25. Two position DC tone control using change of pin 5 resistance (muting function)

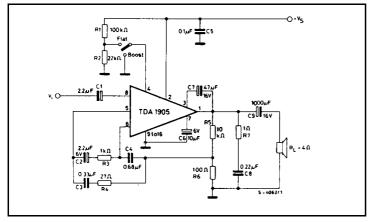


Figure 27. Bass Bomb tone control using change of pin 5 resistance (muting function)

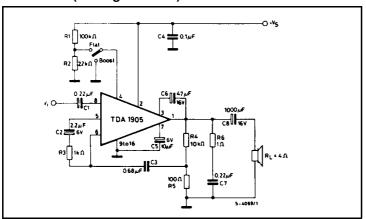


Figure 24. Output power vs. supply voltage (circuit of fig. 23)

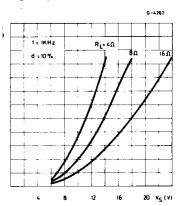


Figure 26. Frequency response of the circuit of fig. 25

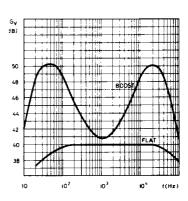
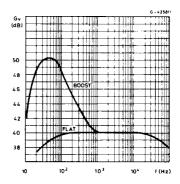


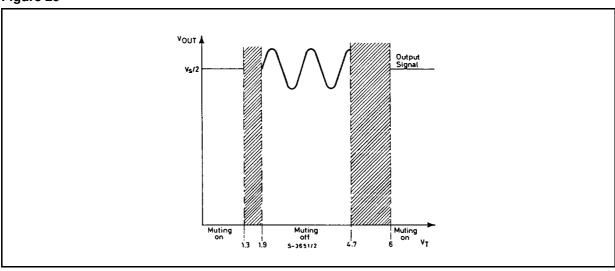
Figure 28. Frequency response of the circuit of fig. 27



MUTING FUNCTION

The output signal can be inhibited applying a DC voltage V_T to pin 4, as shown in fig. 29

Figure 29



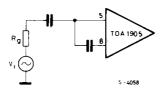
The input resistance at pin 5 depends on the threshold voltage V_T at pin 4 and is typically:

$$R_5 = 200 \text{ K}\Omega$$

$$R_5 = 200 \text{ K}\Omega$$
 @ $1.9 \text{V} \leq \text{V}_T \leq 4.7 \text{V}$

$$R5 = 10 \Omega$$

Referring to the following input stage, the possible attenuation of the input signal and therefore of the output



$$A_T = \frac{V_i}{V_8} = \frac{R_g + (\frac{R_8 \cdot R_5}{R_8 + 5})}{(\frac{R_8 \cdot R_5}{R_8 + R_5})}$$

where R8 \cong 100 K Ω

Considering $R_g = 10 \text{ K}\Omega$ the attenuation in the muting-on condition is typically A_T = 60 dB. In the muting-off condition, the attenuation is very low, typically 1.2 dB.

A very low current is necessary to drive the threshold voltage V_T because the input resistance at pin 4 is greater than 150 K Ω . The muting function can be used in many cases, when a temporary inhibition of the output signal is requested, for example:

- in switch-on condition, to avoid preamplifier power-on transients (see fig. 22)

- during switching at the input stages.
- during the receiver tuning.

The variable impedance capability at pin 5 can be useful in many applications and two examples are shown in fig. 25 and 27, where it has been used to change the feedback network, obtaining 2 different frequency responses.

APPLICATION SUGGESTION

The recommended values of the external components are those shown on the application circuit of fig. 21. When the supply voltage V_{S} is less than 10V, a 100Ω resistor must be connected between pin 2 and pin 3 in order to obtain the maximum output power. Different values can be used. The following table can help the designer.

Component	Raccom.	Purpose	Larger than	Smaller than	Allowed range	
Component	value	Fulpose	recommended value	recommended value	Min.	Max.
R _g + R ₁	10ΚΩ	Input signal imped. for muting operation	Increase of the attenuation in muting-on condition. Decrease of the input sensitivity.	Decrease of the attenuation in muting on condition.		
R ₂	10ΚΩ	Feedback resistors	Increase of gain.	Decrease of gain. Increase quiescent current.	9 R ₃	
R ₃	100Ω		Decrease of gain.	Increase of gain.		1ΚΩ
R ₄	1ΚΩ	Frequency stability	Danger of oscillation at high frequencies with inductive loads.			
R ₅	100Ω	Increase of the output swing with low supply voltage.			47	330
P ₁	20ΚΩ	Volume potentiometer	Increase of the switch-on noise.	Decrease of the input impedance and of the input level.	10ΚΩ	100ΚΩ
C ₁ C ₂ C ₃	0.22μF	Input DC decoupling.	Higher cost lower noise.	Higher low frequency cutoff. Higher noise.		
C ₄	2.2μF	Inverting input DC decoupling.	Increase of the switch- on noise.	Higher low frequency cutoff.	0.1μF	
C ₅	0.1μF	Supply voltage bypass.		Danger of oscillations.		
C ₆	10μF	Ripple rejection	Increase of SVR increase of the switch-on time	Degradation of SVR	2.2μF	100μF
C ₇	47μF	Bootstrap.		Increase of the distortion at low frequency.	10μF	100μF
C ₈	0.22μF	Frequency stability.		Danger of oscillation.		
C ₉	1000μF	Output DC decoupling.		Higher low frequency cutoff.		

THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- 1) An overload on the output (even if it is permanent), or an above limit ambient temperature can be easily tolerated since the Tj cannot be higher than 150 °C.
- 2) The heatsink can have a smaller factor of safety compared with that of a conventional circuit. There is no possibility of device damage due to high junction temperature. If for any reason, the junction temperature increases up to 150 °C, the thermal shut-down simply reduces the power dissipation and the current consumption.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 32 shows this dissipable power as a function of ambient temperature for different thermal resistance.

Figure 31. Output power

and drain current vs. case

temperature

Figure 30. Output power and drain current vs. case temperature

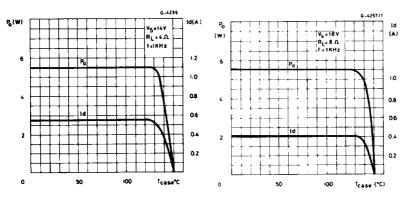
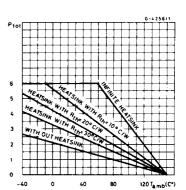


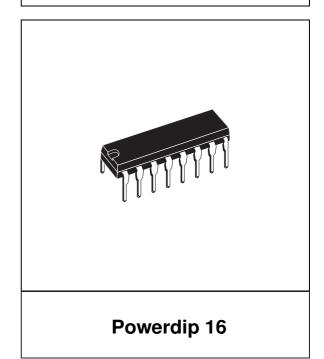
Figure 32. Maximum allowable power dissipation vs. ambient temperature

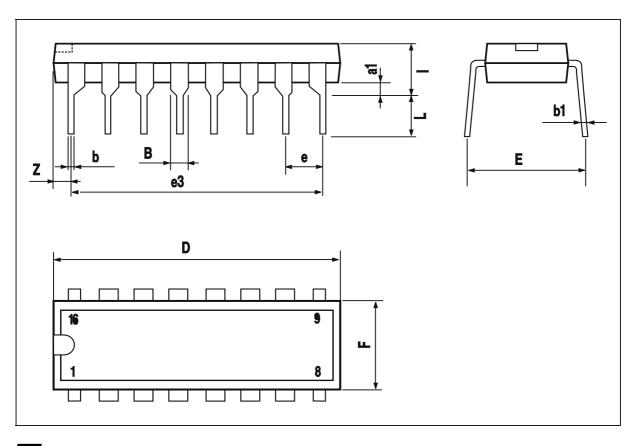


MOUNTING INSTRUCTION: See TDA1904

DIM.		mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.85		1.40	0.033		0.055	
b		0.50			0.020		
b1	0.38		0.50	0.015		0.020	
D			20.0			0.787	
Е		8.80			0.346		
е		2.54			0.100		
e3		17.78			0.700		
F			7.10			0.280	
I			5.10			0.201	
L		3.30			0.130		
Z			1.27			0.050	

OUTLINE AND MECHANICAL DATA





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